

## 60V, 11A, 90mΩ N-Channel Power MOSFET

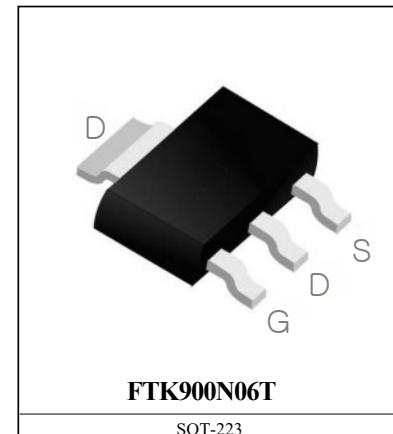
## FEATURES

- 100% UIS and R<sub>g</sub> tested
- Logic-level gate drive
- Fast switching
- RoHS Compliant
- Halogen-Free according to IEC 61249-2-21

## APPLICATIONS

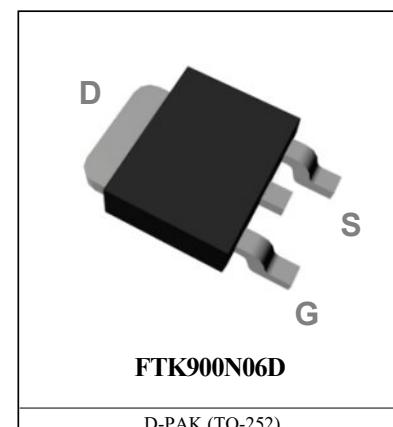
- DC-DC Converters
- Solenoid and Motor Drivers

PRODUCT SUMMARY		
PARAMETER	VALUE	UNIT
V <sub>DS</sub>	60	V
R <sub>DS(on)</sub> (max)	V <sub>GS</sub> = 10V	110
	V <sub>GS</sub> = 4.5V	130
Q <sub>g</sub>	V <sub>GS</sub> = 10V	nC



FTK900N06T

SOT-223



FTK900N06D

D-PAK (TO-252)

Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current (Note 1)	T <sub>C</sub> = 25°C	22	A
	T <sub>C</sub> = 100°C	7	
Pulsed Drain Current (Note 2)	I <sub>DM</sub>	44	A
Single Pulse Avalanche Current (Note 3)	I <sub>AS</sub>	7	A
Single Pulse Avalanche Energy (Note 3)	E <sub>AS</sub>	25	mJ
Total Power Dissipation	T <sub>C</sub> = 25°C	SOT-223	W
		TO-252	20
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C

## THERMAL RESISTANCE

PARAMETER	SYMBOL	MAXIMUM	UNIT
Thermal Resistance – Junction to Case	SOT-223	R <sub>θJC</sub>	16
	TO-252	R <sub>θJC</sub>	6
Thermal Resistance – Junction to Ambient	SOT-223	R <sub>θJA</sub>	70
	TO-252	R <sub>θJC</sub>	62

Note: R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design.



ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ C$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	$BV_{DSS}$	60	--	--	V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu A$	$V_{GS(TH)}$	0.8	1.4	2.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	$I_{GSS}$	--	--	$\pm 100$	nA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 60V$	$I_{DSS}$	--	--	1	$\mu A$
	$V_{GS} = 0V, V_{DS} = 48V$ $T_J = 125^\circ C$		--	--	10	
Drain-Source On-State Resistance (Note 4)	$V_{GS} = 10V, I_D = 3A$	$R_{DS(on)}$	--	90	110	$m\Omega$
	$V_{GS} = 4.5V, I_D = 1.5A$		--	110	130	
<b>Dynamic</b>						
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 30V,$ $I_D = 3A$	$Q_g$	--	11	--	nC
Gate-Source Charge		$Q_{gs}$	--	1.4	--	
Gate-Drain Charge		$Q_{gd}$	--	1.8	--	
Input Capacitance	$V_{GS} = 0V, V_{DS} = 30V,$ $f = 1.0MHz$	$C_{iss}$	--	525	--	pF
Output Capacitance		$C_{oss}$	--	30	--	
Reverse Transfer Capacitance		$C_{rss}$	--	24	--	
Gate Resistance	$f = 1.0MHz$	$R_g$	--	1.7	--	$\Omega$
<b>Switching</b> (Note 5)						
Turn-On Delay Time	$V_{GS} = 10V, V_{DS} = 30V,$ $I_D = 3A, R_G = 1.5\Omega$	$t_{d(on)}$	--	6.5	--	ns
Rise Time		$t_r$	--	12	--	
Turn-Off Delay Time		$t_{d(off)}$	--	16	--	
Fall Time		$t_f$	--	1.8	--	
<b>Source-Drain Diode</b>						
Diode Forward Voltage (Note 4)	$V_{GS} = 0V, I_S = 3A$	$V_{SD}$	--	--	1.2	V
Reverse Recovery Time	$I_S = 3A, V_{GS} = 30V$ $di/dt = 100A/\mu s$	$t_{rr}$	--	14	--	ns
Reverse Recovery Charge		$Q_{rr}$	--	10	--	nC

**Notes:**

- Limited by maximum junction temperature.
- Pulsed width limited by maximum junction temperature.
- $L = 1mH, V_{GS} = 10V, R_G = 25\Omega$ , Starting  $T_J = 25^\circ C$ .
- Pulse test: Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- Switching time is essentially independent of operating temperature.

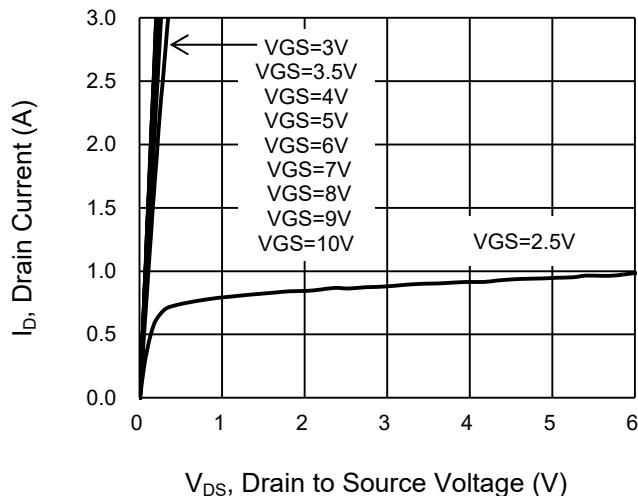
**ORDERING INFORMATION**

ORDERING CODE	PACKAGE	PACKING
FTK900N06T	SOT-223	4.0kpcs / 13 " Reel
FTK900N06D	TO-252	2.5kpcs / 13 " Reel

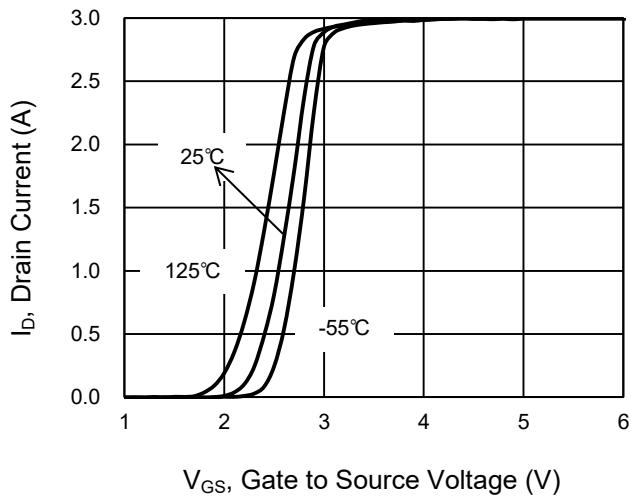
## CHARACTERISTICS CURVES

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

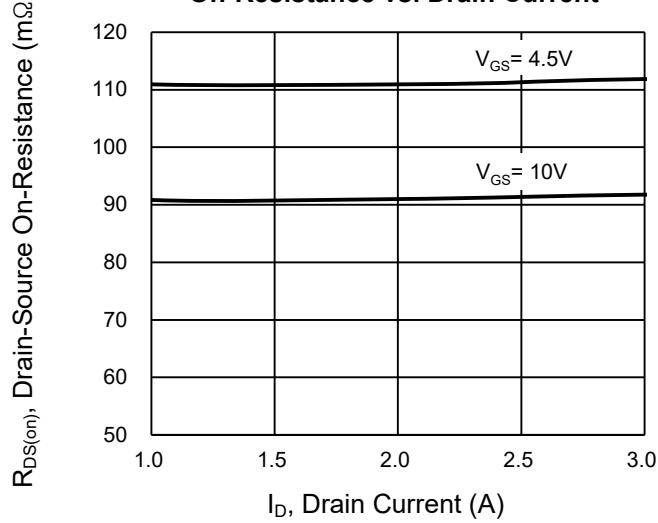
**Output Characteristics**



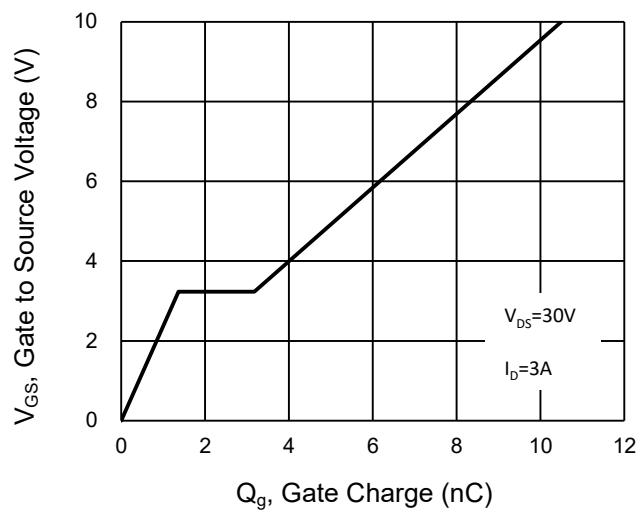
**Transfer Characteristics**



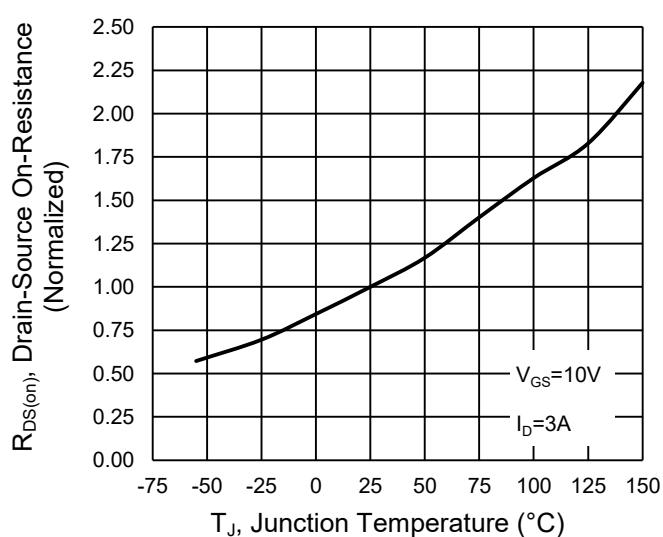
**On-Resistance vs. Drain Current**



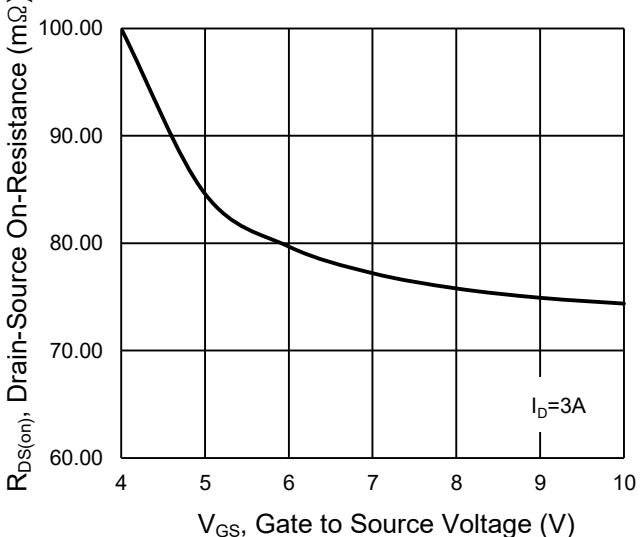
**Gate-Source Voltage vs. Gate Charge**



**On-Resistance vs. Junction Temperature**



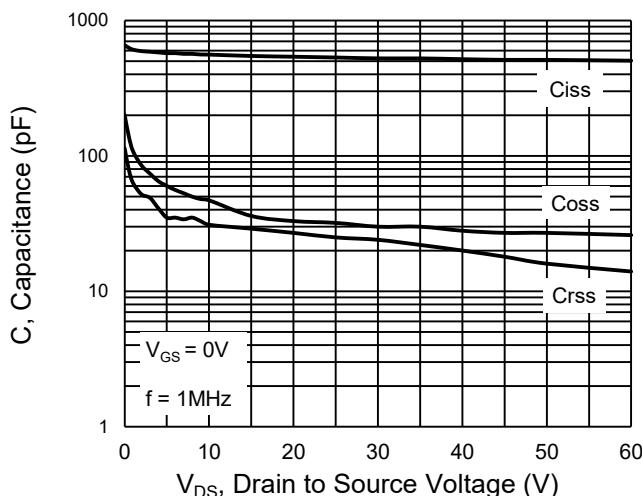
**On-Resistance vs. Gate-Source Voltage**



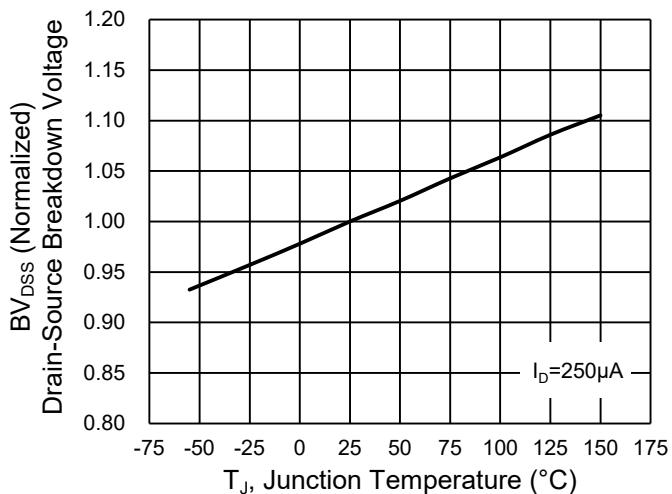
## CHARACTERISTICS CURVES

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

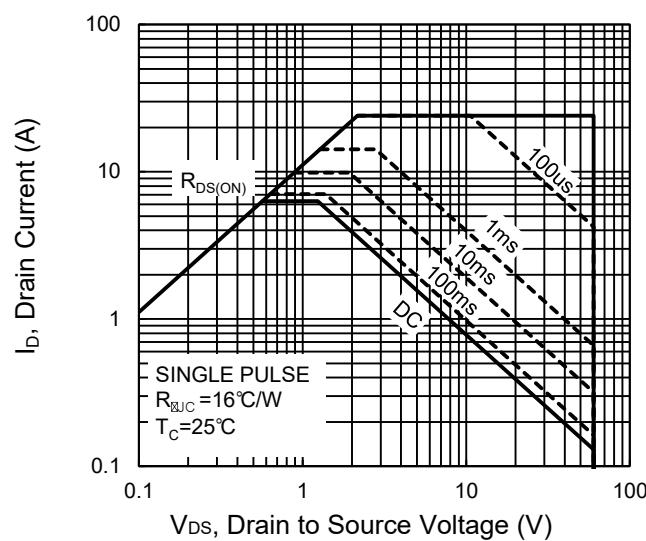
**Capacitance vs. Drain-Source Voltage**



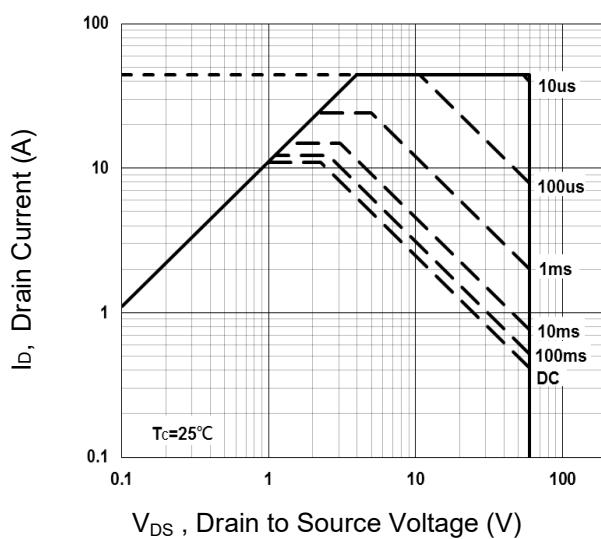
**$\text{BV}_{DSS}$  vs. Junction Temperature**



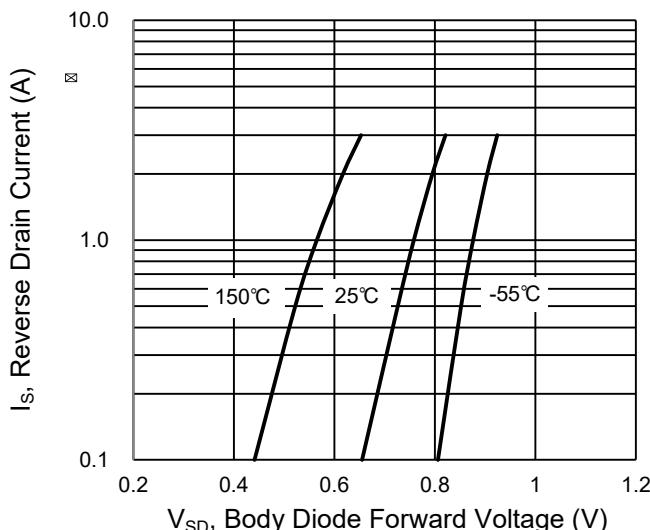
**Maximum Safe Operating Area, Junction-to-Case(SOT-223)**



**Maximum Safe Operating Area, Junction-to-Case(TO-252)**

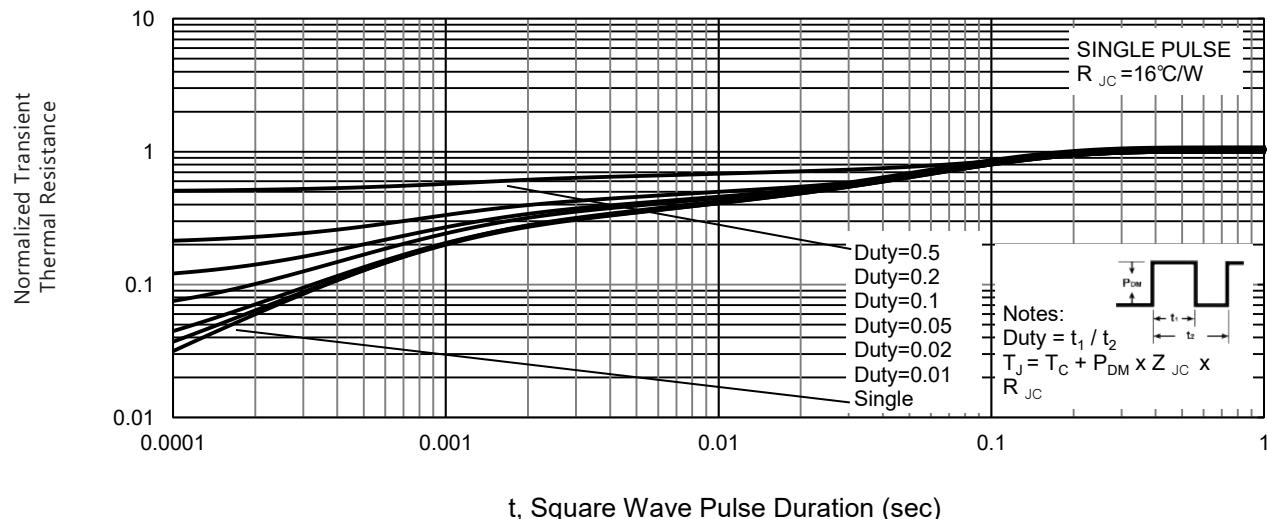
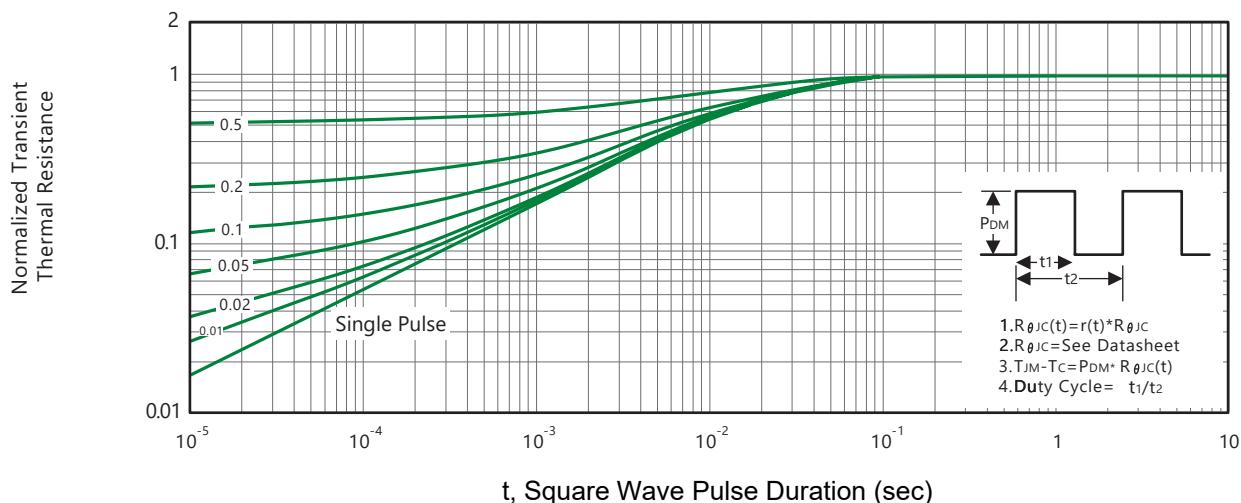


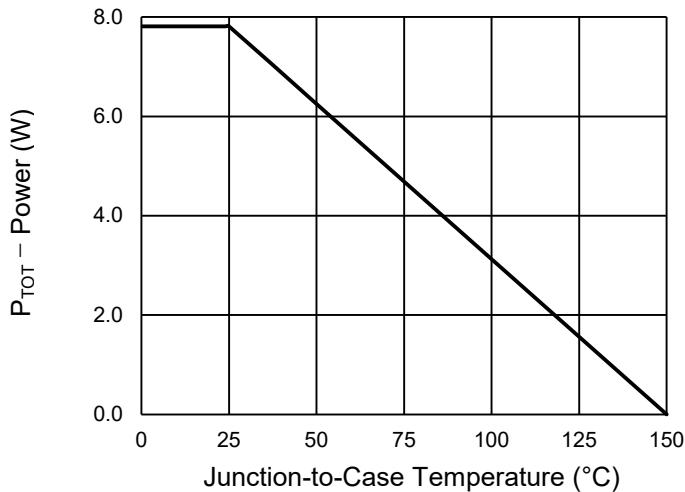
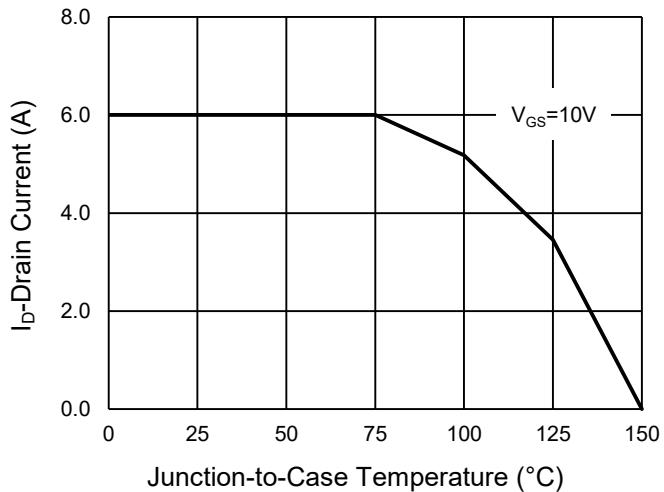
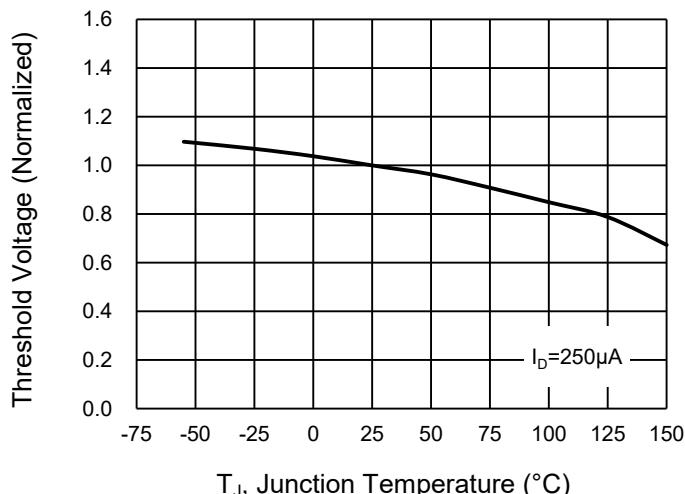
**Source-Drain Diode Forward Current vs. Voltage**



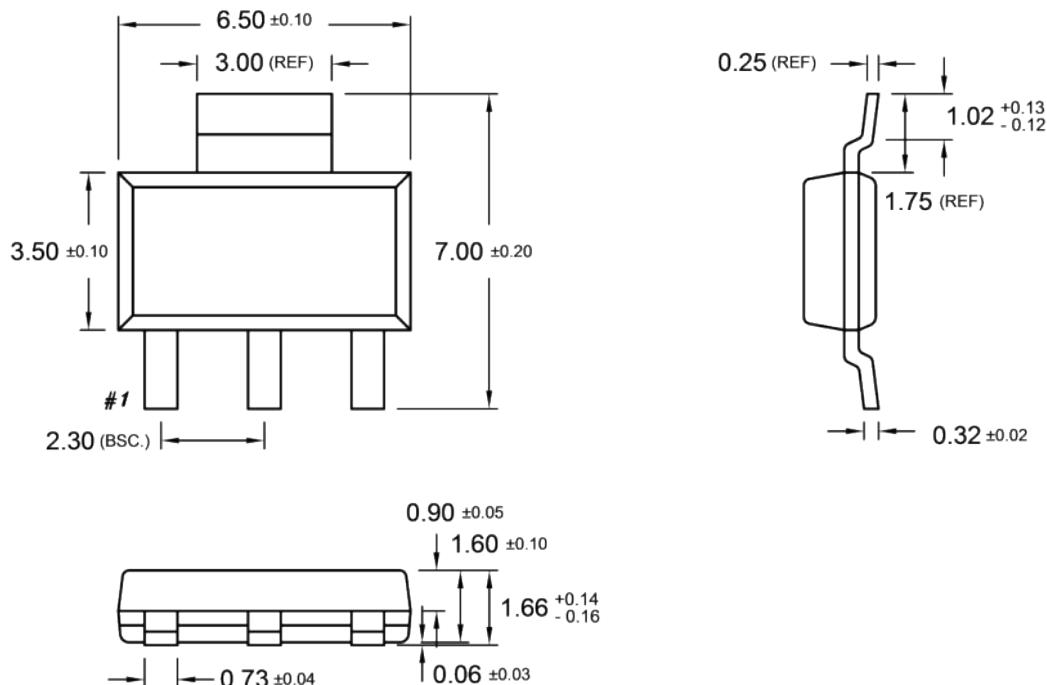
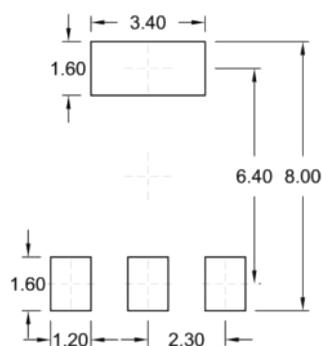
**CHARACTERISTICS CURVES**

(TA = 25°C unless otherwise noted)

**Normalized Thermal Transient Impedance, Junction-to-Cas (SOT-223)****Normalized Thermal Transient Impedance, Junction-to-Cas (TO-252)**

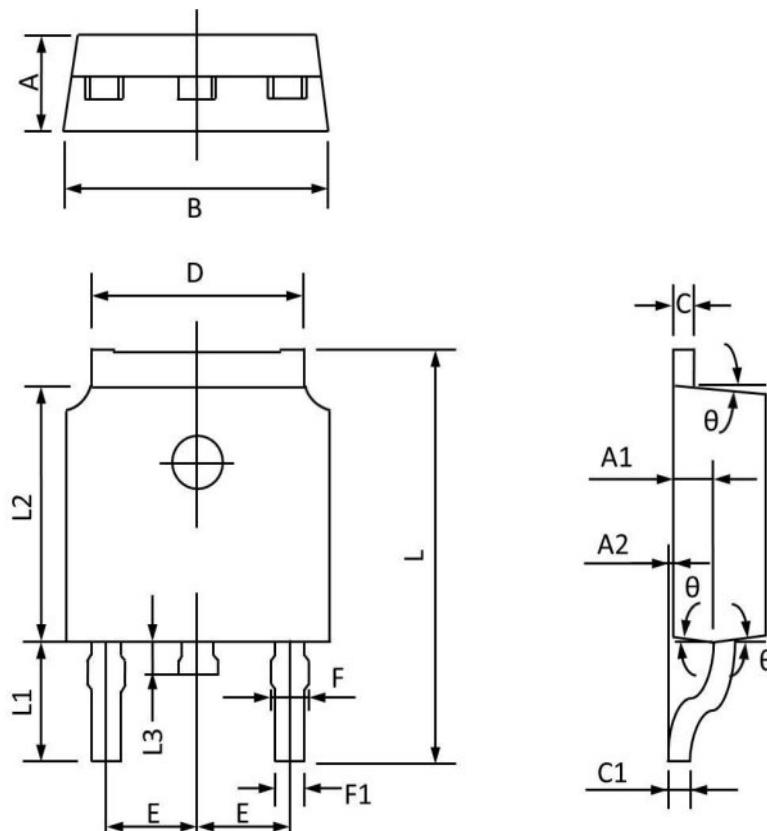
**CHARACTERISTICS CURVES**(T<sub>A</sub> = 25°C unless otherwise noted)**Power Dissipation (SOT-223)****Drain Current (SOT-223)****Normalized gate threshold voltage vs Temperature**

**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)

**SOT-223**

**SUGGESTED PAD LAYOUT** (Unit: Millimeters)


**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)

TO-252



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	2.450	2.150	0.096	0.085
A1	1.200	0.910	0.047	0.036
A2	0.150	0.000	0.006	0.000
B	6.800	6.300	0.268	0.248
C	0.580	0.350	0.023	0.014
C1	0.550	0.380	0.022	0.015
D	5.500	5.100	0.217	0.201
E	2.390	2.000	0.094	0.079
F	0.940	0.600	0.037	0.024
F1	0.860	0.500	0.034	0.020
L	10.400	9.400	0.409	0.370
L1	3.000	2.400	0.118	0.094
L2	6.200	5.300	0.244	0.209
L3	1.200	0.600	0.047	0.024
θ	9°	3°	9°	3°